

# PJQ4464AP-AU

## 60V N-Channel Enhancement Mode MOSFET

**Voltage**

**60 V**

**Current**

**33 A**

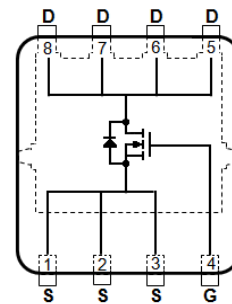
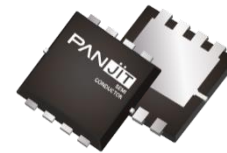
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@16A<17m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@8A<20m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

DFN3333-8L



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>(Note 4)</sup>	$T_C=25^\circ\text{C}$	$I_D$	33	A
	$T_C=100^\circ\text{C}$		21	
Pulsed Drain Current <sup>(Note 1)</sup>	$T_C=25^\circ\text{C}$	$I_{DM}$	132	
Power Dissipation	$T_C=25^\circ\text{C}$	$P_D$	48	W
	$T_C=100^\circ\text{C}$		24	
Continuous Drain Current <sup>(Note 4)</sup>	$T_A=25^\circ\text{C}$	$I_D$	7.3	A
	$T_A=70^\circ\text{C}$		5.9	
Power Dissipation	$T_A=25^\circ\text{C}$	$P_D$	2.4	W
	$T_A=70^\circ\text{C}$		1.6	
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		$E_{AS}$	45	mJ
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~175	$^\circ\text{C}$
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{\theta JC}$	3.1	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature

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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.7	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =16A	-	13	17	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A	-	16	20	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>Dynamic</b> (Note 5)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V(Note 2,3)	-	13.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.8	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	4.9	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	1574	-	pF
Output Capacitance	C <sub>oss</sub>		-	118	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	77	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω (Note 2,3)	-	11	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	11	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	35	-	
Turn-Off Fall Time	t <sub>f</sub>		-	8.1	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	33	A
Reverse Recovery Time	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.68	1	V

**NOTES :**

1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> = 25°C.
4. The maximum current rating is package limited.
5. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. The test condition is L=0.1mH, I<sub>AS</sub>=30A, V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, Starting T<sub>J</sub>=25°C.
7. Guaranteed by design, not subject to production testing.

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## TYPICAL CHARACTERISTIC CURVES

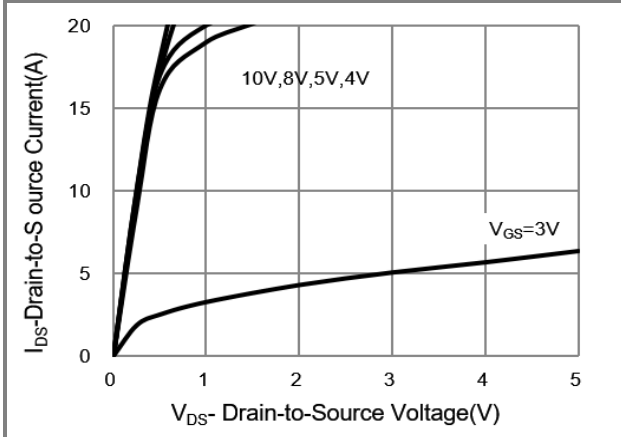


Fig.1 On-Region Characteristics

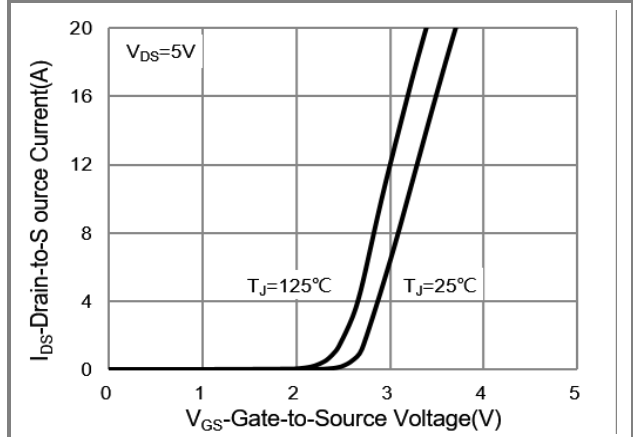


Fig.2 Transfer Characteristics

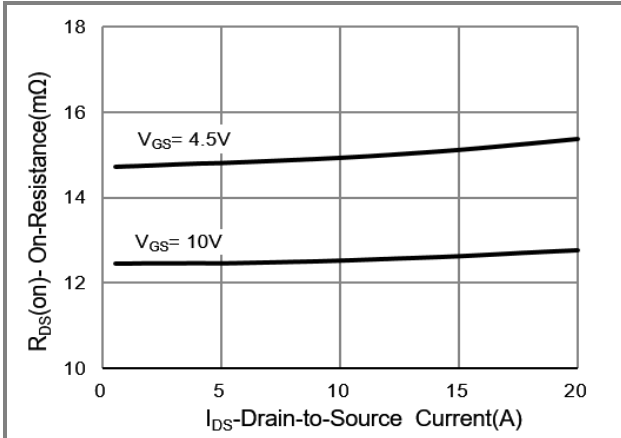


Fig.3 On-Resistance vs. Drain Current

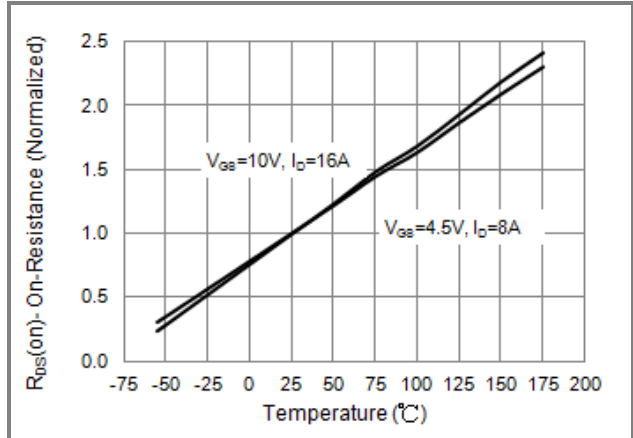


Fig.4 On-Resistance vs. Junction temperature

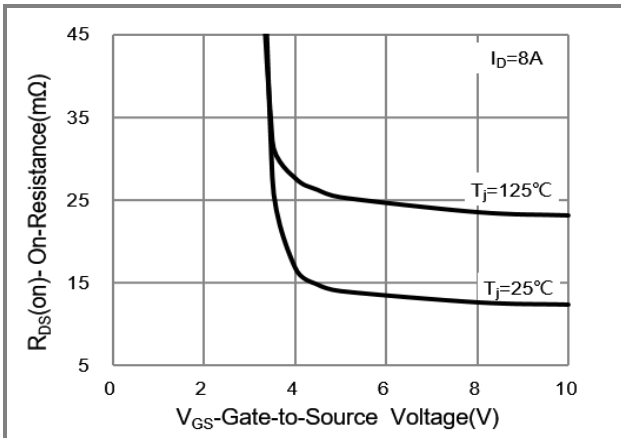


Fig.5 On-Resistance Variation with  $V_{GS}$

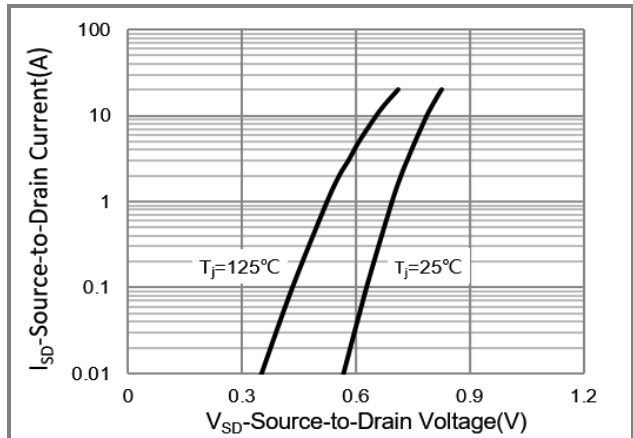
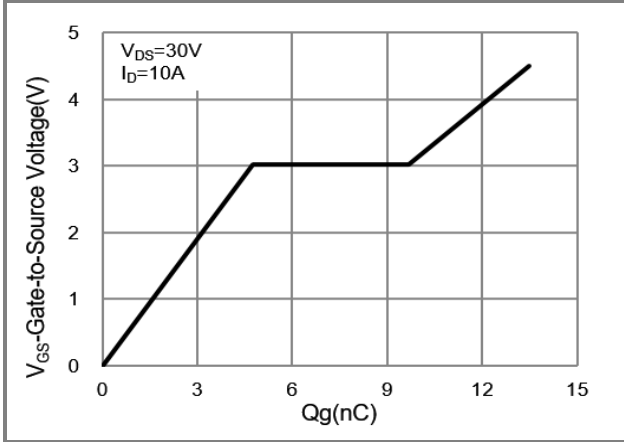


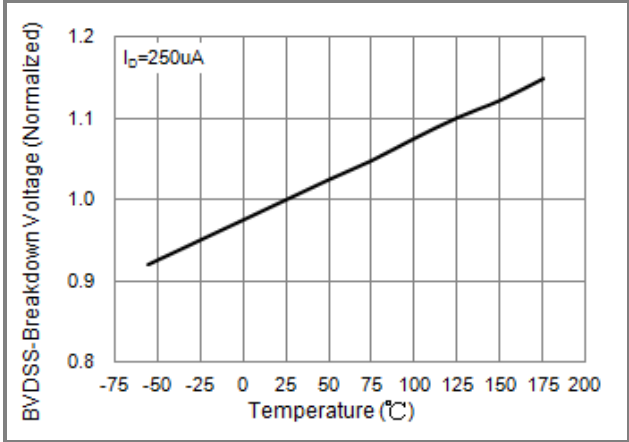
Fig.6 Source-Drain Diode Forward Voltage

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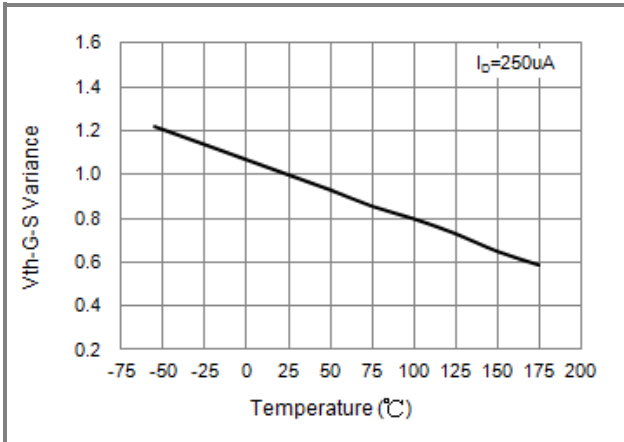
## TYPICAL CHARACTERISTIC CURVES



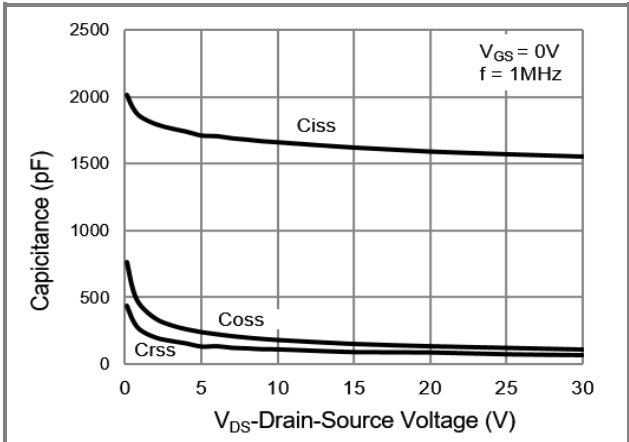
**Fig.7 Gate-Charge Characteristics**



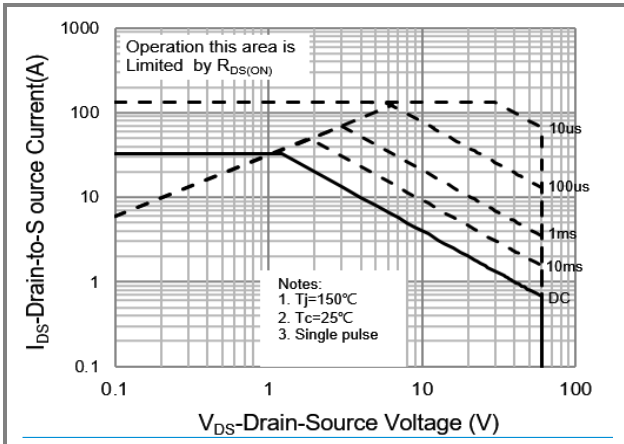
**Fig.8 Breakdown Voltage Variation vs. Temperature**



**Fig.9 Threshold Voltage Variation with Temperature**



**Fig.10 Capacitance vs. Drain-Source Voltage**



**Fig.11 Maximum Safe Operating Area**

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## TYPICAL CHARACTERISTIC CURVES

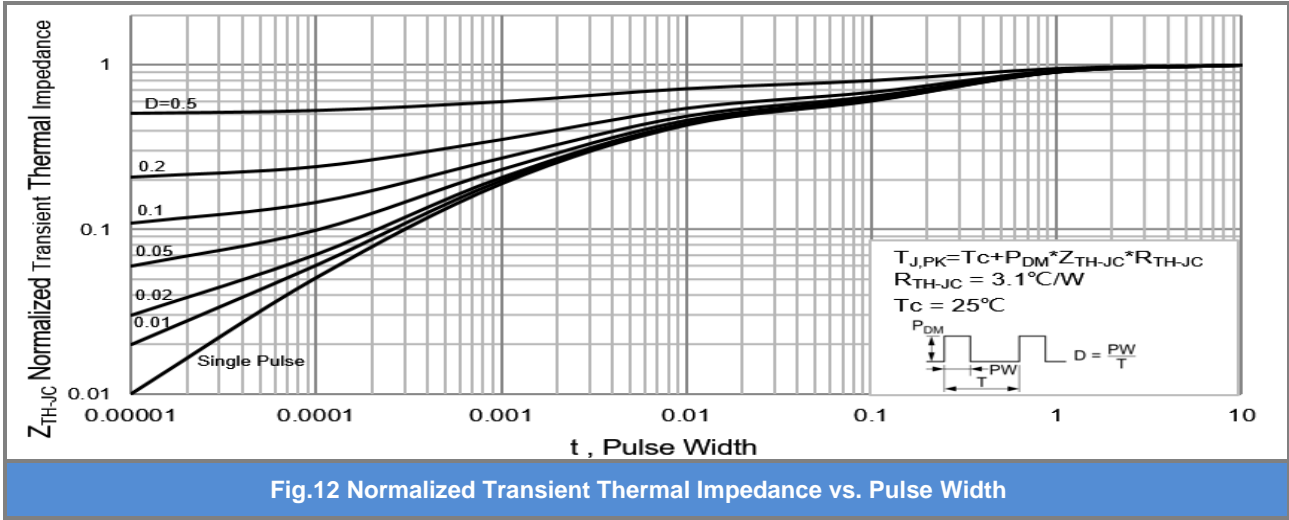


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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